



Docket No. 740756-2297

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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TECHNOLOGY CENTER 28000

In re Patent Application of:

Shunpei YAMAZAKI et al.

Serial No. 09/837,558

Filed: April 19, 2001

For: **SEMICONDUCTOR DEVICE AND  
MANUFACTURING METHOD THEREOF**

)

) Group Art Unit: 2814

) Examiner: Ngan V. Ngo

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) Date: September 20, 2002

**RESPONSE TO RESTRICTION REQUIREMENT AND AMENDMENT**

Commissioner for Patents  
Washington, D.C. 20231

Sir:

In response to the Official Action of August 26, 2002, Applicants respond as follows:

**IN THE CLAIMS:**

Please cancel claims 17-30 without prejudice or disclaimer to file a divisional application directed thereto.

Please add new claims 33-50 as follows:

--33. A method of manufacturing a semiconductor device comprising:

forming a conductive film over a substrate;

patterning said conductive film to form at least one first wiring, said first wiring including at least one first gate electrode;

forming a first insulating film over said first wiring and said substrate;

forming a first semiconductor island and a second semiconductor island wherein said first semiconductor island is located over said first gate electrode with said first insulating film